

## Features

- 30V/40A,
- $R_{DS(ON)} = 10.8\text{m}\Omega$  (max.) @  $V_{GS}=10\text{V}$
- $R_{DS(ON)} = 12\text{m}\Omega$  (max.) @  $V_{GS}=4.5\text{V}$
- $R_{DS(ON)} = 16\text{m}\Omega$  (max.) @  $V_{GS}=2.5\text{V}$
- 100% UIS+Rg tested
- Reliable and Rugged
- Lead Free and Green Devices Available  
(RoHS Compliant)

## Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.
- Application for NB Adapter in.

## Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

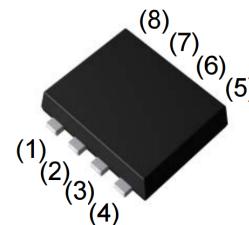
Symbol	Parameter	Rating	Unit
<b>Common Ratings</b>			
$V_{DSS}$	Drain-Source Voltage	30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 12$	
$T_J$	Maximum Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	
$I_S$	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$	10
$I_D$	Continuous Drain Current	$T_C=25^\circ\text{C}$	40
		$T_C=100^\circ\text{C}$	26
$I_{DM}$	Pulsed Drain Current	$T_C=25^\circ\text{C}$	90
$P_D$	Maximum Power Dissipation	$T_C=25^\circ\text{C}$	32
		$T_C=100^\circ\text{C}$	12.8
$R_{\theta JC}$	Thermal Resistance-Junction to Case	Steady State	$^\circ\text{C}/\text{W}$
$I_D$	Continuous Drain Current	$T_A=25^\circ\text{C}$	9
		$T_A=70^\circ\text{C}$	7
$I_{DM}$	Pulsed Drain Current	$T_A=25^\circ\text{C}$	36
$P_D^a$	Maximum Power Dissipation	$T_A=25^\circ\text{C}$	1.5
		$T_A=70^\circ\text{C}$	1
$R_{\theta JA}^{b,c}$	Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$	$^\circ\text{C}/\text{W}$
		Steady State	84
$I_{AS}^d$	Avalanche Current, Single pulse	$L=0.1\text{mH}$	A
$E_{AS}^d$	Avalanche Energy, Single pulse	$L=0.1\text{mH}$	mJ

Note a :  $R_{\theta JA}$  steady state  $t=999\text{s}$ .

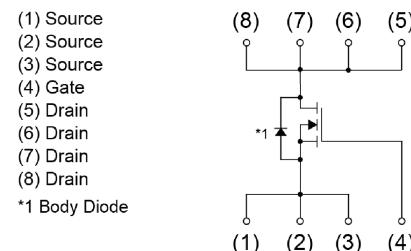
Note b :  $t \leq 10\text{s}$  and surface mounted on FR-4 board using  $1\text{in}^2$  pad, 2 oz Cu.

Note c : Steady time = 999s and surface mounted on FR-4 board using  $1\text{in}^2$  pad, 2 oz Cu.

Note d : UIS tested and pulse width limited by maximum junction temperature  $150^\circ\text{C}$  (initial temperature  $T_j=25^\circ\text{C}$ ).



DFN5x6A-8\_EP



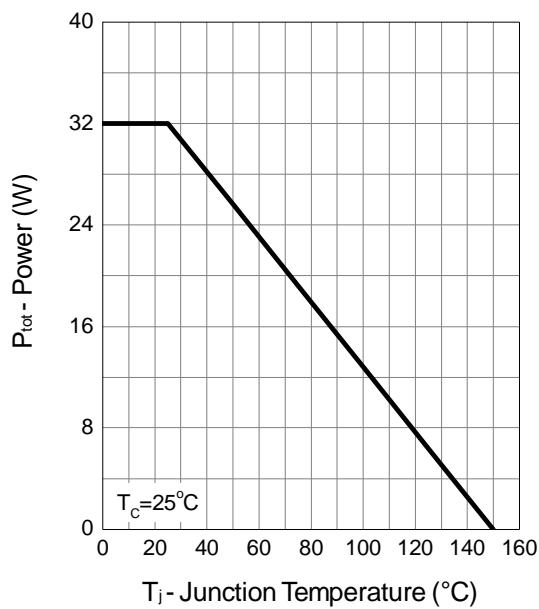
**Electrical Characteristics** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_{DS}=250\mu\text{A}$	30	-	-	V
$BV_{DSST}$	Drain-Source Breakdown Voltage (transient)	$V_{GS}=0\text{V}, I_{D(\text{aval})}=20\text{A}$ $T_{case}=25^\circ\text{C}, t_{\text{transient}}=100\text{ns}$	34	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=24\text{V}, V_{GS}=0\text{V}$ $T_J=85^\circ\text{C}$	-	-	1	$\mu\text{A}$
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu\text{A}$	0.5	0.85	1.3	V
$I_{GSS}$	Gate Leakage Current	$V_{GS}=\pm 12\text{V}, V_{DS}=0\text{V}$	-	-	$\pm 100$	nA
$R_{DS(\text{ON})}^e$	Drain-Source On-state Resistance	$V_{GS}=10\text{V}, I_{DS}=10\text{A}$	-	9	10.8	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_{DS}=7\text{A}$	-	9.6	12	
		$V_{GS}=2.5\text{V}, I_{DS}=5\text{A}$	-	12	16	
$G_{fs}$	Forward Transconductance	$V_{DS}=25\text{V}, I_{DS}=20\text{A}$	-	45	-	S
<b>Diode Characteristics</b>						
$V_{SD}^e$	Diode Forward Voltage	$I_{SD}=3\text{A}, V_{GS}=0\text{V}$	-	0.75	1.3	V
$t_{rr}$	Reverse Recovery Time	$I_{SD}=10\text{A}, dI_{SD}/dt=100\text{A}/\mu\text{s}$	-	12.2	-	ns
$t_a$	Charge Time		-	7.5	-	
$t_b$	Discharge Time		-	4.6	-	
$Q_{rr}$	Reverse Recovery Charge		-	5.6	-	
<b>Dynamic Characteristics</b>						
$R_G$	Gate Resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, F=1\text{MHz}$	-	2.4	4.3	$\Omega$
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=15\text{V},$ Frequency=1.0MHz	-	1150	1500	$\text{pF}$
$C_{oss}$	Output Capacitance		-	120	-	
$C_{rss}$	Reverse Transfer Capacitance		-	85	-	
$t_{d(\text{ON})}$	Turn-on Delay Time	$V_{DD}=15\text{V}, R_L=15\Omega,$ $I_{DS}=1\text{A}, V_{GEN}=10\text{V},$ $R_G=6\Omega$	-	9.6	18	ns
$t_r$	Turn-on Rise Time		-	10	18	
$t_{d(\text{OFF})}$	Turn-off Delay Time		-	29	53	
$t_f$	Turn-off Fall Time		-	4.5	8	
<b>Gate Charge Characteristics</b>						
$Q_g$	Total Gate Charge	$V_{DS}=15\text{V}, V_{GS}=10\text{V},$ $I_{DS}=10\text{A}$	-	25.5	36	$\text{nC}$
$Q_g$	Total Gate Charge	$V_{DS}=15\text{V}, V_{GS}=4.5\text{V},$ $I_{DS}=10\text{A}$	-	11	12	
$Q_{gth}$	Threshold Gate Charge		-	0.85	-	
$Q_{gs}$	Gate-Source Charge		-	2.4	-	
$Q_{gd}$	Gate-Drain Charge		-	3.4	-	

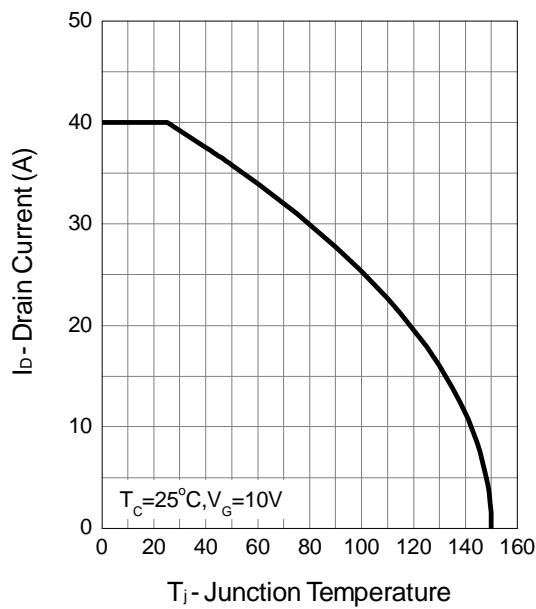
Note e : Pulse test ; pulse width $\leq 300\mu\text{s}$ , duty cycle $\leq 2\%$ .

## Typical Operating Characteristics

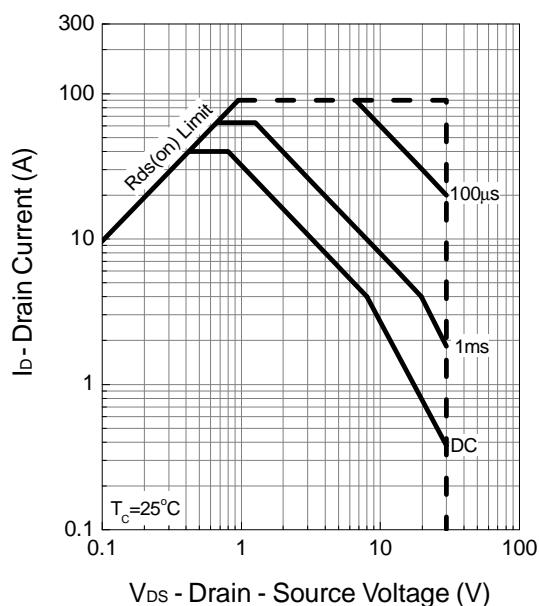
**Power Dissipation**



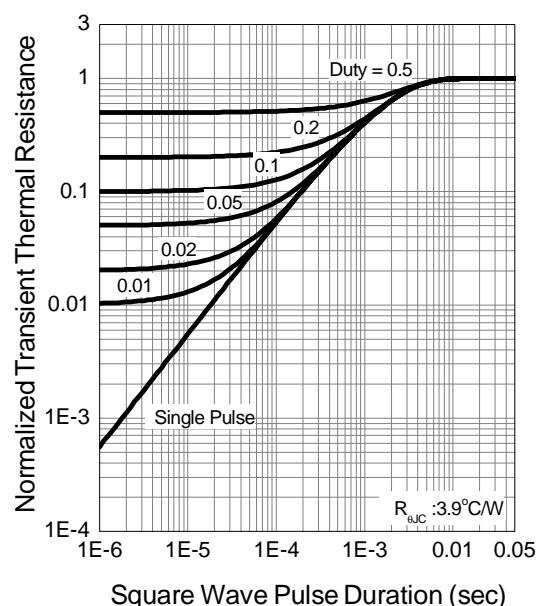
**Drain Current**



**Safe Operation Area**

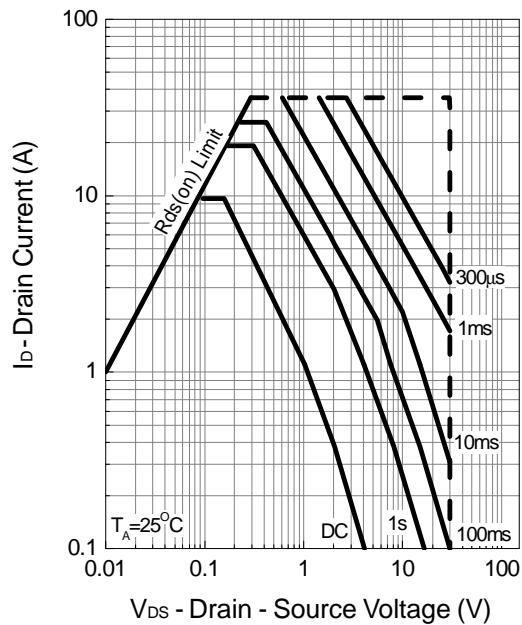


**Thermal Transient Impedance**

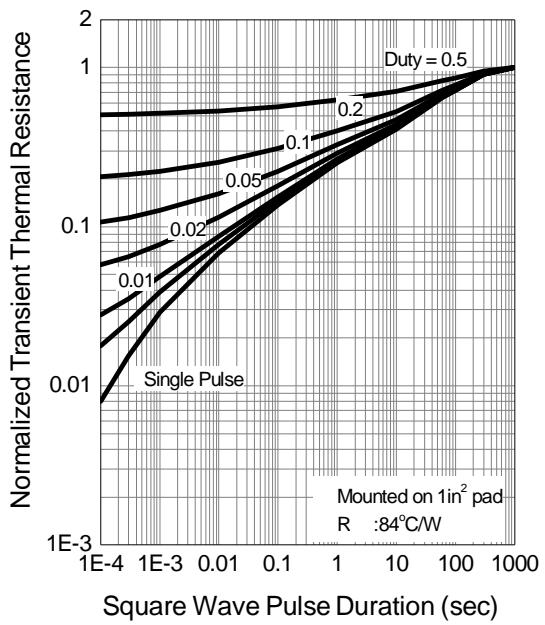


## Typical Operating Characteristics (Cont.)

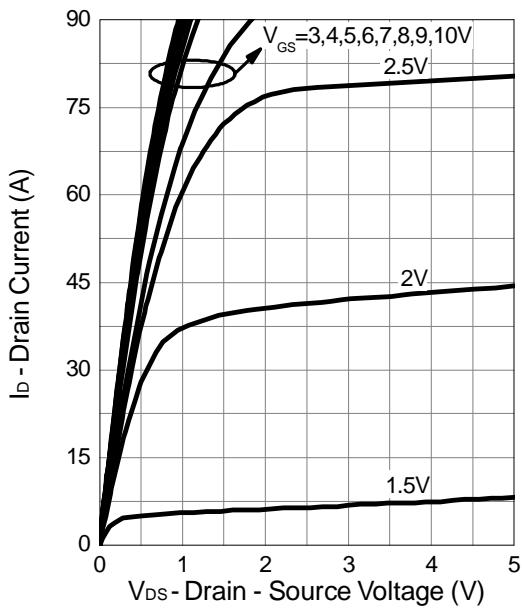
**Safe Operation Area**



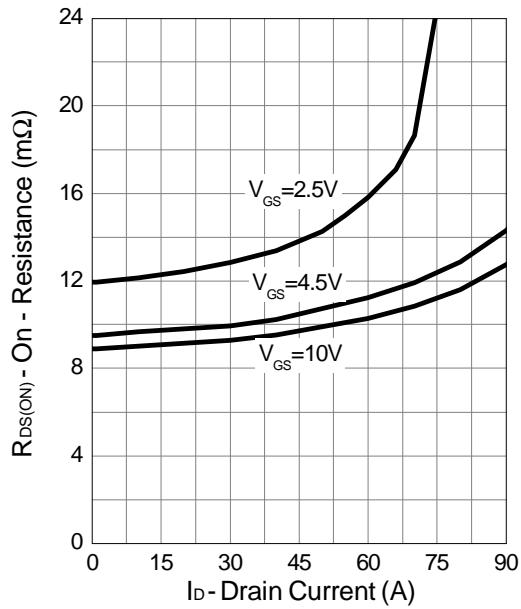
**Thermal Transient Impedance**



**Output Characteristics**

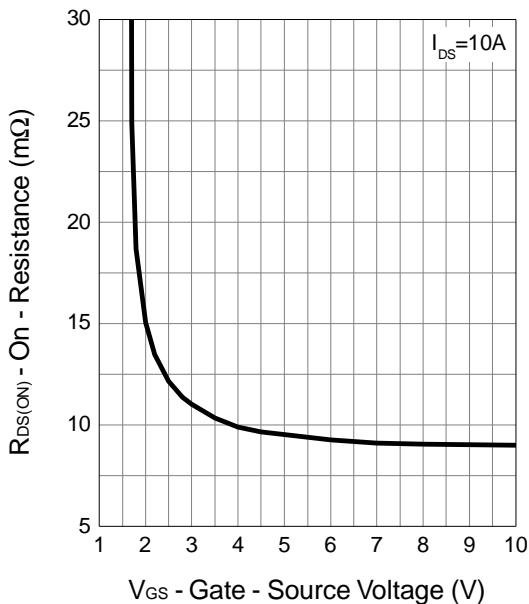


**Drain-Source On Resistance**

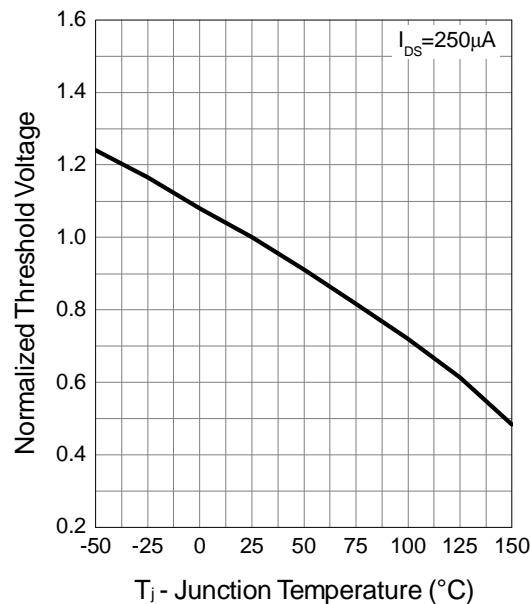


## Typical Operating Characteristics (Cont.)

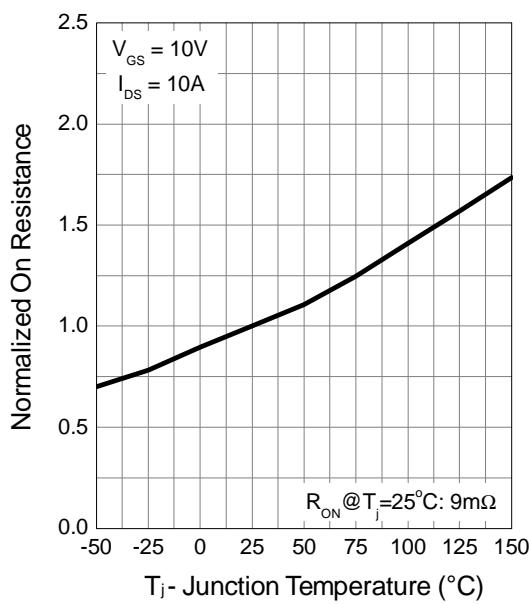
**Gate-Source On Resistance**



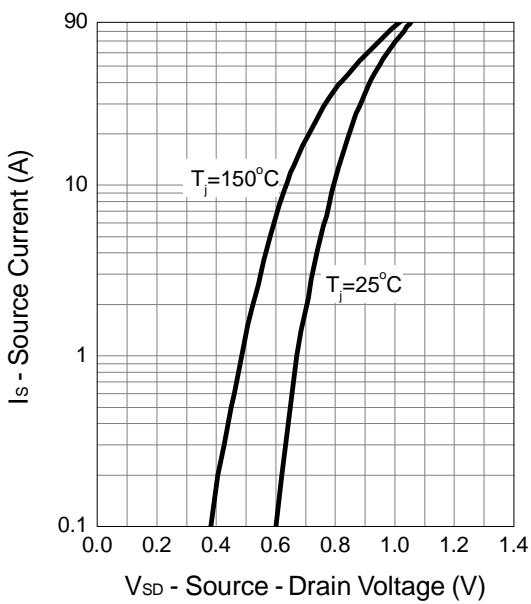
**Gate Threshold Voltage**



**Drain-Source On Resistance**

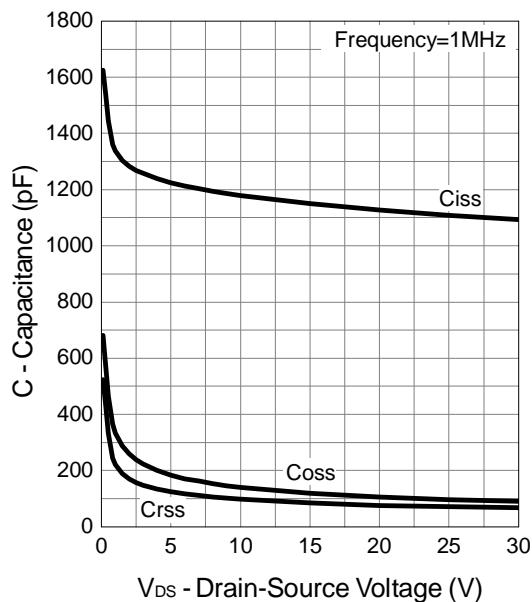


**Source-Drain Diode Forward**

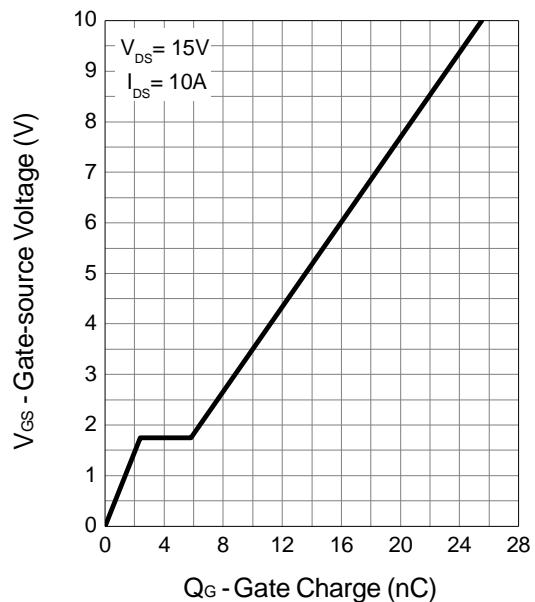


## Typical Operating Characteristics (Cont.)

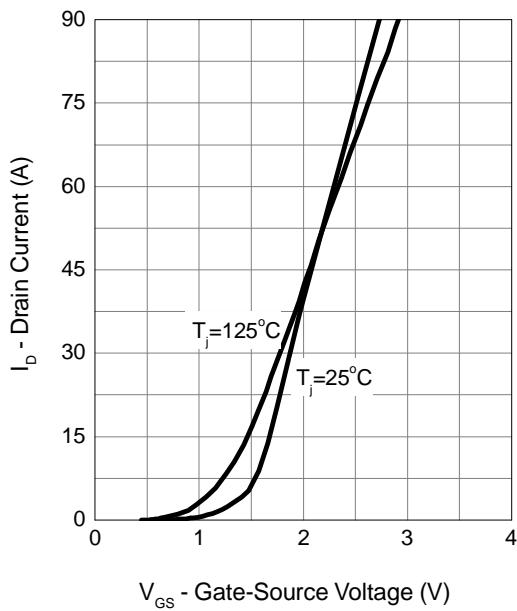
**Capacitance**



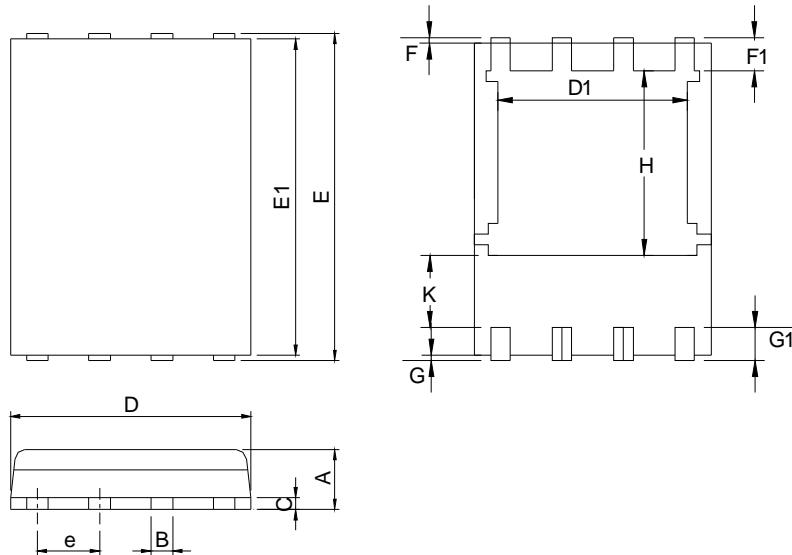
**Gate Charge**



**Transfer Characteristics**



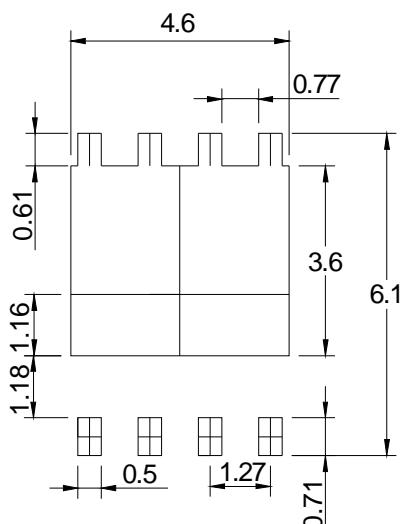
## Package Information



SYMBOL	DFN5x6A-8_EP			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.90	1.20	0.035	0.047
B	0.3	0.51	0.012	0.020
C	0.19	0.25	0.007	0.010
D	4.80	5.30	0.189	0.209
D1	4.00	4.40	0.157	0.173
E	5.90	6.20	0.232	0.244
E1	5.50	5.80	0.217	0.228
e	1.27 BSC		0.050 BSC	
F	0.05	0.30	0.002	0.012
F1	0.35	0.75	0.014	0.030
G	0.05	0.30	0.002	0.012
G1	0.35	0.75	0.014	0.030
H	3.34	3.9	0.131	0.154
K	0.762	-	0.03	-

Note : 1. Dimension D, D1,D2 and E1 do not include mold flash or protrusions.  
Mold flash or protrusions shall not exceed 10 mil.

### RECOMMENDED LAND PATTERN



UNIT: mm



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